600V Super Junction Power MOSFET

- ★ Super_Junction technology
- ★ Much lower Ron*A performance for On-state efficiency
- ★ Better efficiency due to very low FOM
- ★ Qualified for industrial grade applications according to JEDEC

Product Summary

Green

BVDSS	RDSON	ID
600V	530mΩ	7A

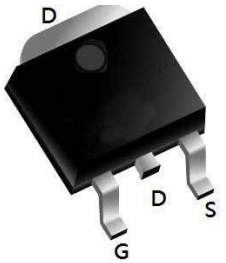
Description

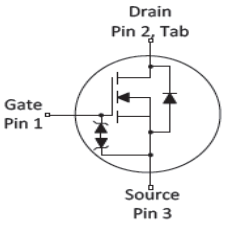
The XR60R500 use super junction technology and design to provide excellent RDS(ON) with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

The XR60R500 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

ESD(HBM):2000V

TO252-3L Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	±30	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	7	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	4	A
I_{DM}	Pulsed Drain Current[2]	27	A
EAS	Single Pulse Avalanche Energy[3]	55	mJ
I_{AS}	Avalanche Current	---	A
P_D@T_C=25℃	Total Power Dissipation[4]	63	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	128	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	2.09	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	600	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	---	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=1A	---	530	600	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	3.0	3.5	4.0	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=600V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=600V, V_{GS}=0V , T_J=100℃	---	---	100	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±30V , V_{DS}=0V	---	---	±80	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=3.5A	---	5	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	17	---	Ω
Q_g	Total Gate Charge	V_{DS}=480V , V_{GS}=10V , I_D=3A	---	10.8	---	nC
Q_{gs}	Gate-Source Charge		---	2.8	---	
Q_{gd}	Gate-Drain Charge		---	5.2	---	
$T_{d(on)}$	Turn-On Delay Time	VGS=10V, VDD=400V, RG=10Ω, ID=3A	---	11	---	ns
T_r	Rise Time		---	25	---	
$T_{d(off)}$	Turn-Off Delay Time		---	35	---	
T_f	Fall Time		---	27	---	
C_{iss}	Input Capacitance	V_{DS}=100V , V_{GS}=0V , f=1MHz	---	317	---	pF
C_{oss}	Output Capacitance		---	22	---	
C_{rss}	Reverse Transfer Capacitance		---	7.8	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	7	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=3.5A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	IF=3.5A , di/dt=100A/μs , T_J=25℃	---	190	---	nS
Q_{rr}	Reverse Recovery Charge		---	1.3	---	uC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
3.The EAS data shows Max. rating . The test condition is TJ = 25℃,VDD=200V,VGS=10V,L=50mH
4.The power dissipation is limited by 150℃ junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Performance Characteristics

Fig 1. Output Characteristics (T_j=25℃)

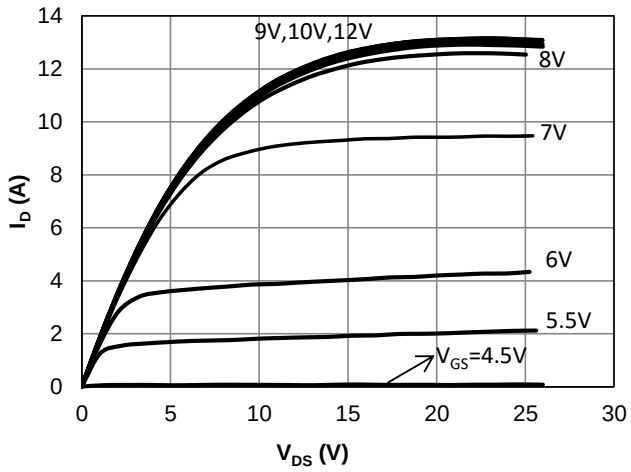


Fig 2. Output Characteristics (T_j=150℃)

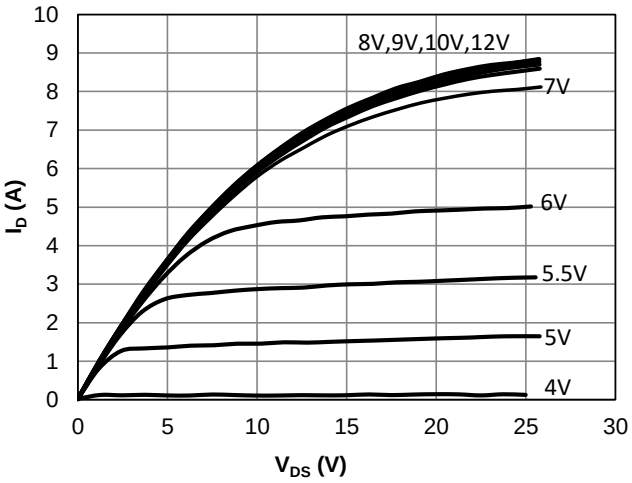


Fig 3: Transfer Characteristics

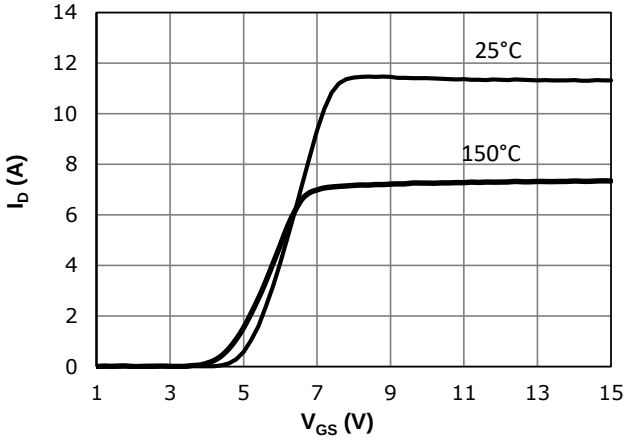


Fig 4: V_{TH} vs. T_j Temperature Characteristics

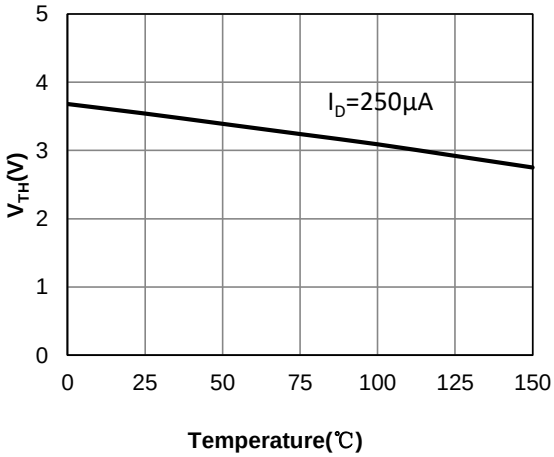


Fig 5: $R_{DS(on)}$ vs. I_{DS} Characteristics(T_j=25℃)

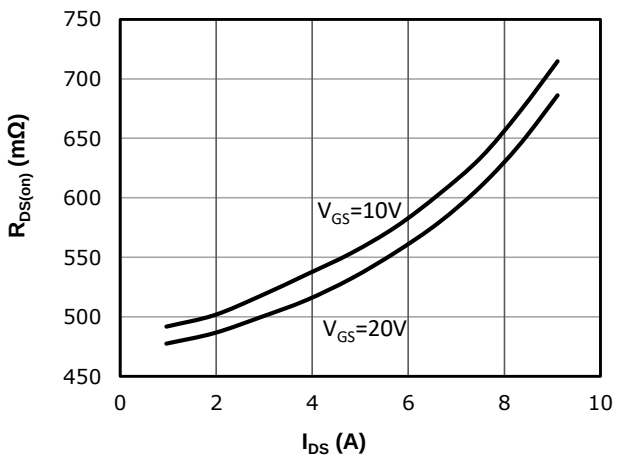


Fig 6: $R_{DS(on)}$ vs. Temperature

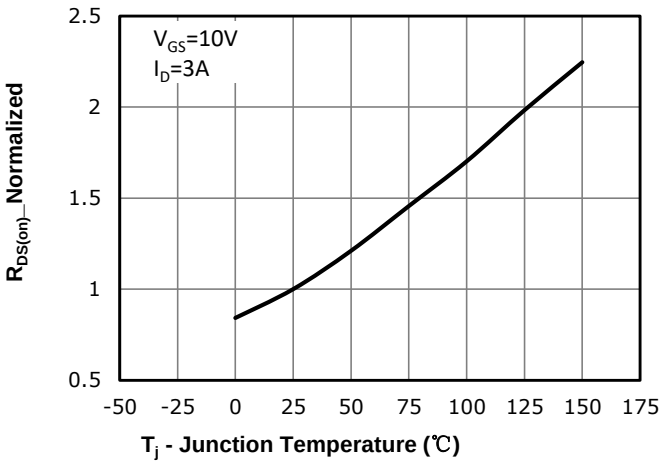


Fig 7: BV_{DSS} vs. Temperature

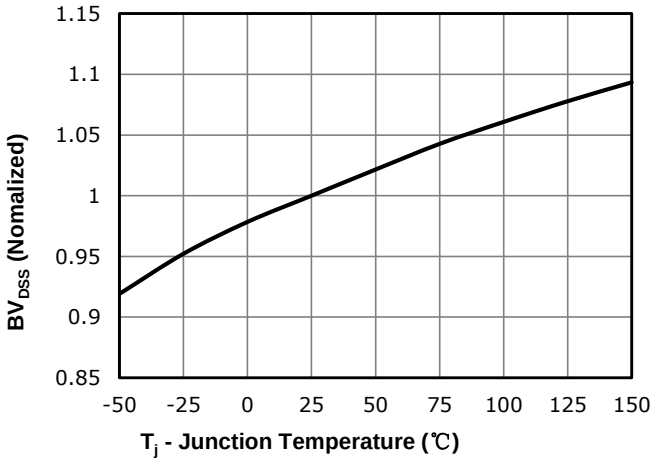


Fig 8: $R_{DS(on)}$ vs. Gate Voltage

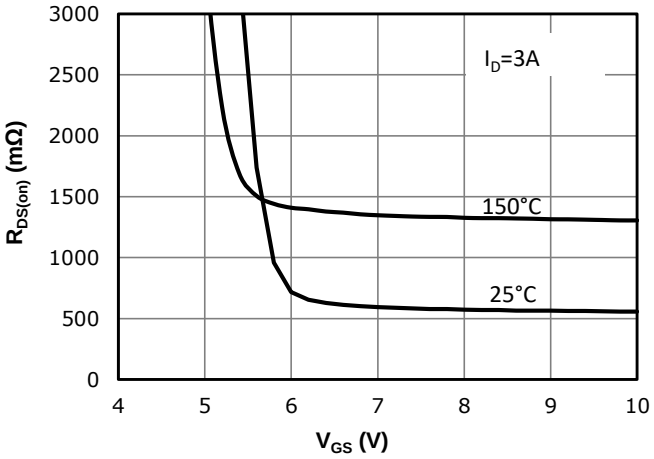


Fig 9: Body-diode Forward Characteristics

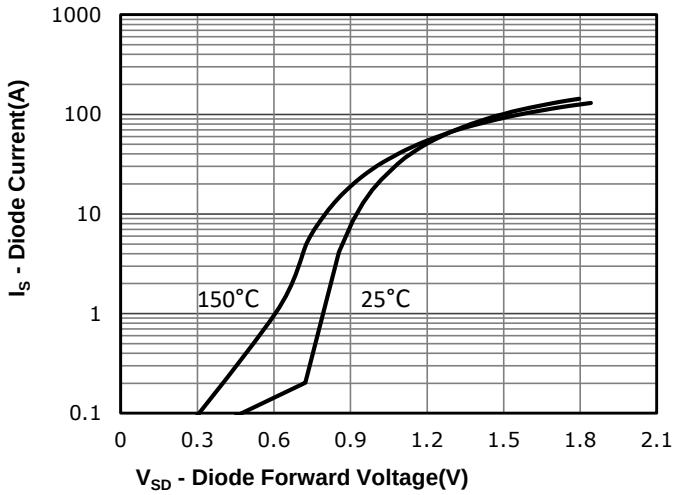


Fig 10: Gate Charge Characteristics

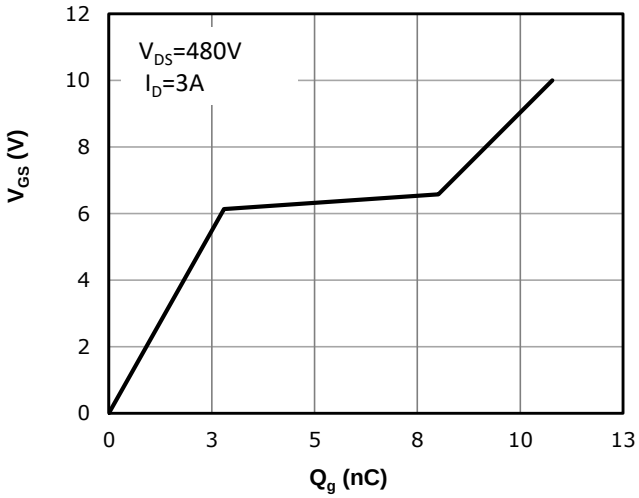


Fig 11: Capacitance Characteristics

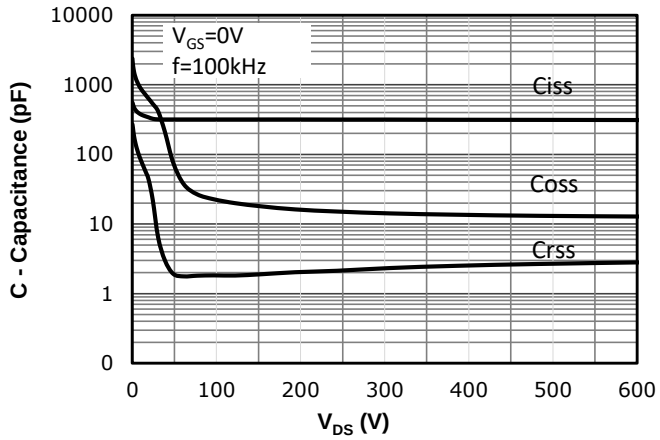


Fig 12: Safe Operating Area

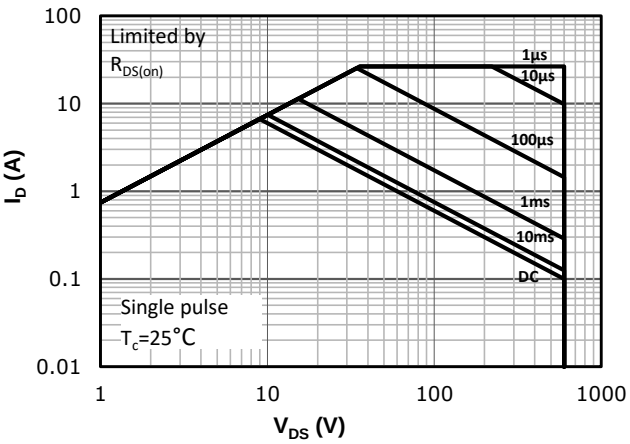
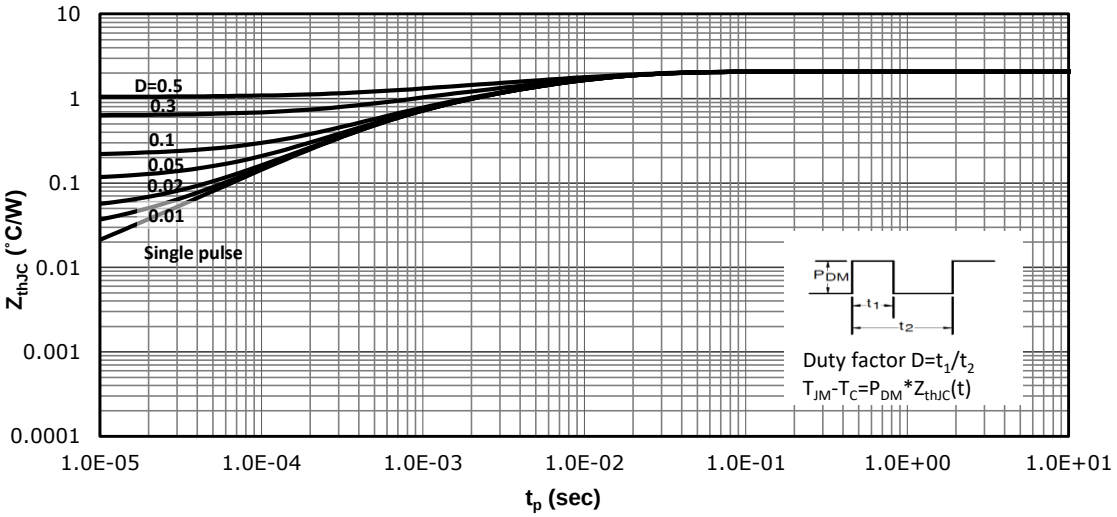
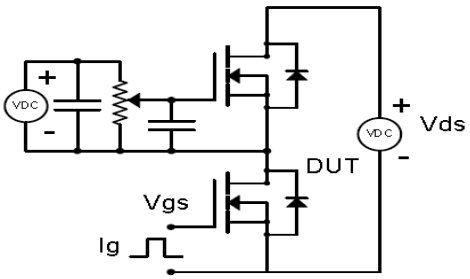


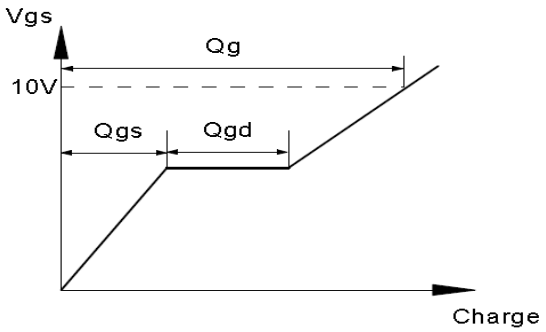
Fig 13: Max. Transient Thermal Impedance



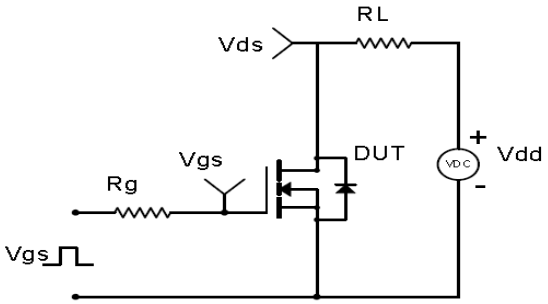
Test Circuit & Waveform

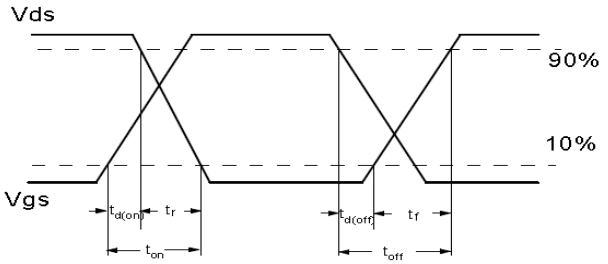
Gate Charge Test Circuit & Waveform



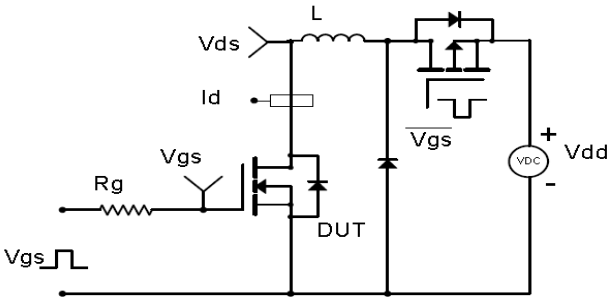


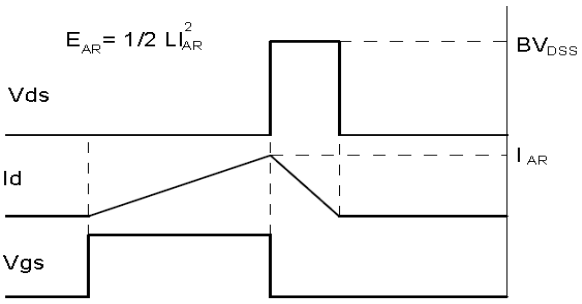
Resistive Switching Test Circuit & Waveforms



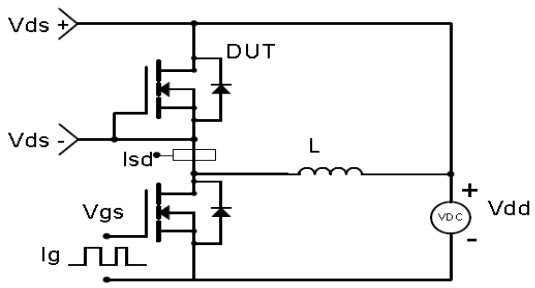


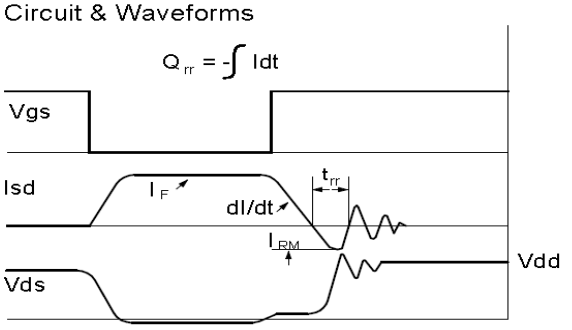
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



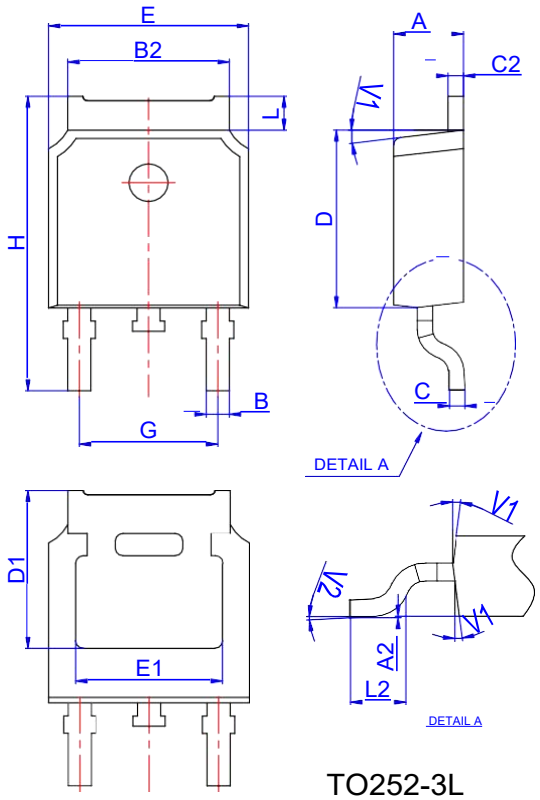


Diode Recovery Test Circuit & Waveforms





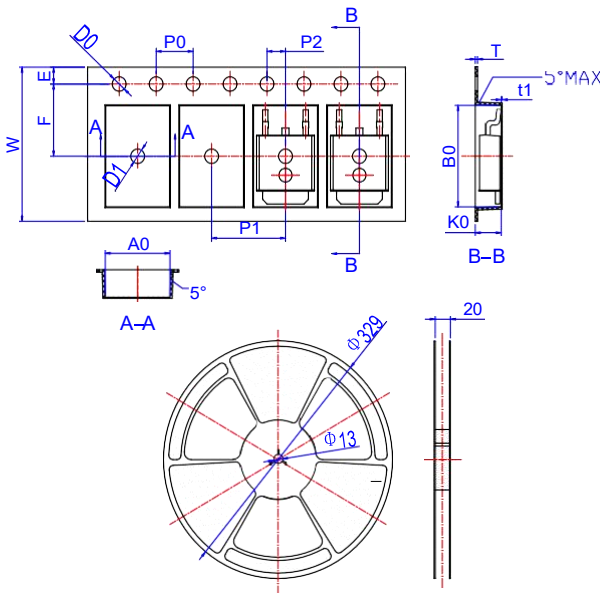
Package Mechanical Data-TO252-3L



TO252-3L

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Spectification-TO252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583